

These miniature surface mount MOSFETs low $R_{DS(on)}$ assure minimal power loss and conserve energy, making these devices ideal for use in small power management circuitry. Typical applications are dc-dc converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low $R_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SC-70/SOT-323 Surface Mount Package Saves Board Space
- Pb-Free Package is Available

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

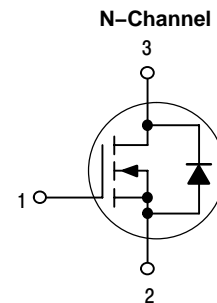
Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	20	Vdc
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	Vdc
Drain Current			mAdc
– Continuous @ $T_A = 25^\circ\text{C}$	I_D	300	
– Continuous @ $T_A = 70^\circ\text{C}$	I_D	240	
– Pulsed Drain Current ($t_p \leq 10 \mu\text{s}$)	I_{DM}	750	
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 1) Derate above 25°C	P_D	150 1.2	mW mW/°C
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	T_L	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

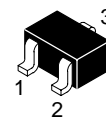
1. Mounted on G10/FR4 glass epoxy board using minimum recommended footprint.

300 mAMPS, 20 VOLTS

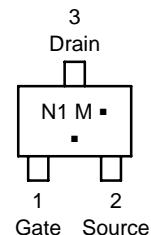
$R_{DS(on)} = 1 \Omega$



MARKING DIAGRAM AND PIN ASSIGNMENT



SC-70/SOT-323
CASE 419
STYLE 8



N1 = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBF2201NT1	SC-70/ SOT-323	3000 Tape & Reel
MMBF2201NT1G	SC-70/ SOT-323 (Pb-Free)	3000 Tape & Reel

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-to-Source Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 10\ \mu\text{A}$)	$V_{(BR)DSS}$	20	–	–	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 16\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) ($V_{DS} = 16\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 125^\circ\text{C}$)	I_{DSS}	–	–	1.0 10	μAdc
Gate-Body Leakage Current ($V_{GS} = \pm 20\text{ Vdc}$, $V_{DS} = 0$)	I_{GSS}	–	–	± 100	nAdc
ON CHARACTERISTICS (Note 2)					
Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{Adc}$)	$V_{GS(th)}$	1.0	1.7	2.4	Vdc
Static Drain-to-Source On-Resistance ($V_{GS} = 10\text{ Vdc}$, $I_D = 300\text{ mAdc}$) ($V_{GS} = 4.5\text{ Vdc}$, $I_D = 100\text{ mAdc}$)	$r_{DS(on)}$	–	0.75 1.0	1.0 1.4	Ω
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 200\text{ mAdc}$)	g_{FS}	–	450	–	mMhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	($V_{DS} = 5.0\text{ V}$)	C_{iss}	–	45	pF
Output Capacitance	($V_{DS} = 5.0\text{ V}$)	C_{oss}	–	25	
Transfer Capacitance	($V_{DG} = 5.0\text{ V}$)	C_{rss}	–	5.0	
SWITCHING CHARACTERISTICS (Note 3)					
Turn-On Delay Time	($V_{DD} = 15\text{ Vdc}$, $I_D = 300\text{ mAdc}$, $R_L = 50\ \Omega$)	$t_{d(on)}$	–	2.5	ns
Rise Time		t_r	–	2.5	
Turn-Off Delay Time		$t_{d(off)}$	–	15	
Fall Time		t_f	–	0.8	
Gate Charge (See Figure 5)		Q_T	–	1400	pC
SOURCE-DRAIN DIODE CHARACTERISTICS					
Continuous Current		I_S	–	–	0.3 A
Pulsed Current		I_{SM}	–	–	0.75
Forward Voltage (Note 3)		V_{SD}	–	0.85	V

2. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

3. Switching characteristics are independent of operating junction temperature.